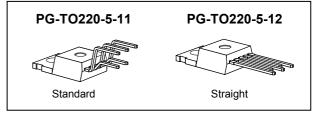


Smart High-Side Power Switch for Industrial Applications One Channel: 38mΩ Status Feedback

Product Summary

On-state Resistance	R _{ON}	38mΩ
Operating Voltage	$V_{bb(on)}$	4.7541V
Nominal load current	I _{L(NOM)}	9.8A
Current limitation	I _{L(SCr)}	40A
Operating Temperature	Ta	-30+85°C

Package



General Description

- N channel vertical power MOSFET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS[®] technology.
- Providing embedded protective functions

Applications

- µC compatible high-side power switch with diagnostic feedback for 5V, 12V and 24V grounded loads in industrial applications
- All types of resistive, inductive and capacitve loads
- Most suitable for loads with high inrush currents, so as lamps
- Replaces electromechanical relays, fuses and discrete circuits

Basic Functions

- Very low standby current
- CMOS compatible input
- Fast demagnetization of inductive loads
- Stable behaviour at undervoltage
- Wide operating voltage range
- Logic ground independent from load ground

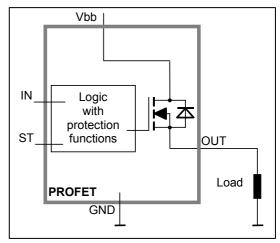
Protection Functions

- Short circuit protection
- Overload protection
- Current limitation
- Thermal shutdown
- Overvoltage protection (including load dump) with external resistor
- Reverse battery protection with external resistor
- Loss of ground and loss of V_{bb} protection
- Electrostatic discharge protection (ESD)

Diagnostic Function

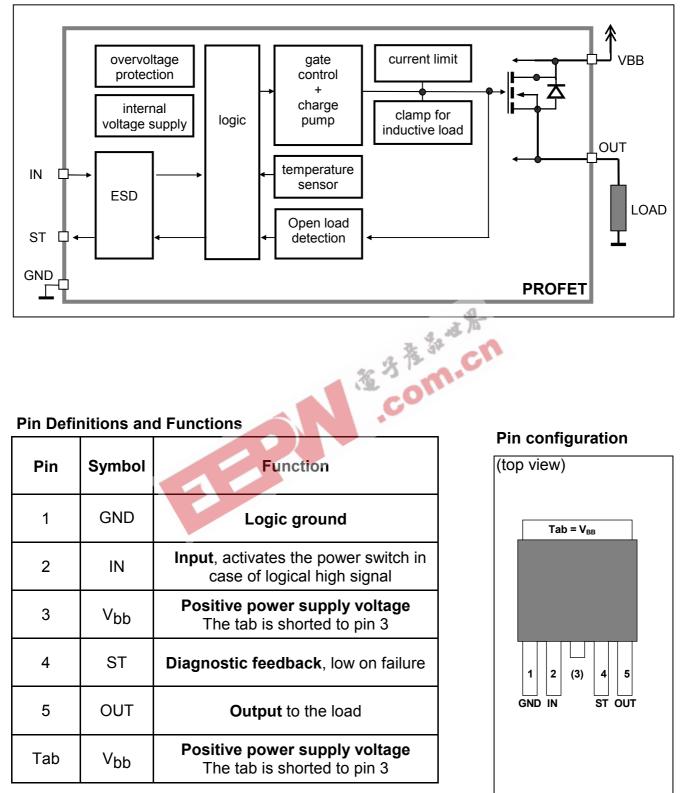
- Diagnostic feedback with open drain output
- Open load detection in ON-state
- Feedback of thermal shutdown in ON-state

Block Diagram





Functional diagram





Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	V _{bb}	43	V
Supply voltage for full short circuit protection <i>T</i> _{j Start} =-40+150°C	V _{bb}	24	V
Load dump protection ¹) $V_{\text{LoadDump}} = V_A + V_s$, $V_A = 13.5 \text{ V}$ $R_1^{2} = 2 \Omega$, $R_L = 4.0 \Omega$, $t_d = 200 \text{ ms}$, IN= low or high	$V_{\sf Load\ dump}^3$	60	V
Load current (Current limit, see page 5)	I _L	self-limited	Α
Junction temperature	Tj	+150	°C
Operating temperature range	Ta	-30 +85	
Storage temperature range	T _{stg}	-40+105	
Power dissipation (DC), $T_C \le 25 \text{ °C}$	P _{tot}	75	W
Maximal switchable inductance, single pulse			
V_{bb} = 12V, $T_{j,start}$ = 150°C, T_{C} = 150°C const. (See diagram on page 8) $I_{L(ISO)}$ = 9.8 A, R _L = 0 Ω, E ⁴⁾ _{AS} =0.33J:	ZL	5.0	mH
Electrostatic discharge capability (ESD) IN: (Human Body Model) ST:	V _{ESD}	1.0 4.0	kV
out to all other pins shorted:	.0	8.0	
acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993; R=1.5kΩ; C=100pF	Se the Mar		
Input voltage (DC)	VIN	-10 +16	V
Current through input pin (DC)	I _{IN}	±2.0	mA
Current through status pin (DC)	I _{ST}	±5.0	
see internal circuit diagrams page 7			
Thermal Characteristics			

Maximum Ratings at $T_i = 25$ °C unless otherwise specified

Parameter and Cont	litions	Symbol		Values	5	Unit
			min	typ	max	
Thermal resistance	chip - case:	<i>R</i> _{thJC}			1.75	K/W
junction - ambient (free air):		<i>R</i> thJA			75	
device on pcb ⁵):				33		

¹⁾ Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins (a 150 Ω resistor for the GND connection is recommended).

²⁾ R_{I} = internal resistance of the load dump test pulse generator ³⁾ $V_{Load dump}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839 ⁴⁾ E_{AS} is the maximum inductive switch-off energy

⁵) Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thick) copper area for V_{bb} connection. PCB is vertical without blown air.



Electrical Characteristics

Parameter and Conditions	Symbol		Values		Unit
at T_j =-40+150°C, V_{bb} = 12 V unless otherwise specified		min	typ	max	

Load Switching Capabilities and Characteristics

On-state resistance (pin	3 to 5)					
I_{L} = 2 A; $V_{BB} \ge 7V$	<i>T</i> j=25 °C:	R _{ON}		35	38	mΩ
	<i>T</i> j=150 °C:			64	72	
see diagram, page 9	,					
Nominal load current, (pi	n 3 to 5)					
ISO 10483-1, 6.7:V _{ON} =0.5V, 7	c=85°C	I _{L(ISO)}	8.8	9.8		A
Output current (pin 5) wh	I _{L(GNDhigh)}			2	mA	
GND pulled up ⁶⁾ , V _{bb} =3	80 V, V _{IN} = 0,					
see diagram page 7						
Turn-on time	IN to 90% V _{OUT} :	<i>t</i> on	50	100	200	μs
Turn-off time	IN 7 to 10% V _{OUT} :	t _{off}	🧶 50	120	250	
$R_{\rm L}$ = 12 Ω ,		- 30.35	JD.			
Slew rate on		dV/dt _{on}	0.1		1	V/µs
10 to 30% V_{OUT} , R_{L} = 12	2 Ω,	S.M.				
Slew rate off		-dV/dt _{off}	0.1		1	V/µs
70 to 40% V_{OUT} , R_{L} = 12	2 Ω,					

Operating Parameters

Operating voltage $T_j = -40$ $T_j = +25+150^{\circ}C:$	V _{bb(on)}	4.75		41	V
/j =+25+150°C:				43	
Overvoltage protection ⁷) $T_i = -40^{\circ}C$:	$V_{\rm bb(AZ)}$	41			V
Overvoltage protection ') $T_j = -40^{\circ}$ C: $I_{bb}=40 \text{ mA}$ $T_j = 25+150^{\circ}$ C:	()	43	47	52	
Standby current (pin 3) T_j =-40+25°C: V_{IN} =0; see diagram on page 9 T_j = 150°C:	I _{bb(off)}		5	8	μA
$V_{\rm IN}$ =0; see diagram on page 9 $T_{\rm j}$ = 150°C:	× ,			25	
Off-State output current (included in <i>I</i> _{bb(off)})	I _{L(off)}		1	10	μA
Vin=0					
Operating current ⁹ , V _{IN} =5 V	I _{GND}		0.8	1.4	mA

⁶) not subject to production test, specified by design

⁷⁾ Supply voltages higher than V_{bb(AZ)} require an external current limit for the GND and status pins (a 150Ω resistor for the GND connection is recommended. See also V_{ON(CL)} in table of protection functions and circuit diagram page 7.

⁸⁾ Measured with load

⁹⁾ Add I_{ST} , if $I_{ST} > 0$, add I_{IN} , if $V_{IN} > 5.5$ V

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				1104	
Parameter and Conditions	Symbol		Values		Unit
at T_j =-40+150°C, V_{bb} = 12 V unless otherwise specified		min	typ	max	
Protection Functions ¹⁰⁾				·	
Current limit (pin 3 to 5)	I _{L(lim)}				
(see timing diagrams on page 11) $T_{\perp} = -40^{\circ} \text{C}$:		46	58	68	Α
(see timing diagrams on page 11) $T_j = -40^{\circ}$ C: $T_j = 25^{\circ}$ C: $T_j = +150^{\circ}$ C:		39 30	51 38	58 46	
Repetitive short circuit shutdown current limit	I _{L(SCr)}	00		10	
$T_{i} = T_{it}$ (see timing diagrams, page 11)	-()		40		А
Thermal shutdown time ¹¹) $T_{j,start} = 25^{\circ}C$:	t _{off(SC)}		1.9		ms
(see timing diagrams on page 11)					
Output clamp (inductive load switch off)		41			
at $V_{OUT} = V_{bb} - V_{ON(CL)}$ $I_L = 40 \text{ mA}$:	V _{ON(CL)}	43	47	52	V
Thermal overload trip temperature	T _{jt}	150			°C
Thermal hysteresis	ΔT_{jt}		10		K
Reverse battery (pin 3 to 1) ¹²⁾	-V _{bb}			32	V
Reverse battery voltage drop $(V_{out} > V_{bb})^{13}$. $I_L = -2 A$ $T_j = 150 $ °C:	-V _{ON(rev)}	8	600		mV
Diagnostic Characteristics	2 34	cn			
Open load detection current (on-condition)	I _{L (OL)}	100		900	mA
Input and Status Feedback ¹⁴⁾		11	I		
Input resistance see circuit page 7	R _I	2.5	3.5	6	kΩ
Input turn-on threshold voltage	V _{IN(T+)}	1.7		3.2	V
Input turn-off threshold voltage	V _{IN(T-)}	1.5			V
Input threshold hysteresis	$\Delta V_{\rm IN(T)}$		0.5		V
Off state input current (pin 2), $V_{IN} = 0.4 V$	I _{IN(off)}	1		50	μA
On state input current (pin 2), $V_{IN} = 5 V$	I _{IN(on)}	20	50	90	μA
Delay time for status with open load after switch off (see timing diagrams on page 11)	t _{d(ST OL4)}	100	520	900	μs
Status output (open drain)					
Zener limit voltage $I_{ST} = +1.6 \text{ mA}$:	$V_{\rm ST(high)}$	5.4	6.1		V
ST low voltage $I_{ST} = +1.6 \text{ mA}$:	V _{ST(low)}			0.4	

¹⁰ Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

¹¹⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.

¹²) Requires 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Note that the power dissipation is higher compared to normal operating conditions due to the voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 3 and circuit page 7).

¹³⁾ not subject to production test, specified by design

¹⁴⁾ If a ground resistor R_{GND} is used, add the voltage drop across this resistor.



Truth Table

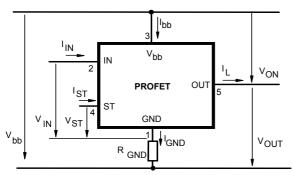
	Input	Output	Status
	level	level	BTS 436L2
Normal	L	L	Н
operation	н	н	н
Open load	L	Z	Н
-	Н	Н	L
Overtem-	L	L	Н
perature	Н	L	L

L = "Low" LevelX = don't careZ = high impedance, potential depends on external circuitH = "High" LevelStatus signal after the time delay shown in the diagrams (see fig 5. page 11)

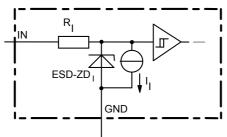




Terms

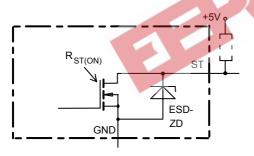


Input circuit (ESD protection)



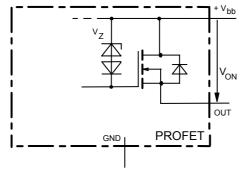
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended

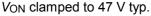
Status output



ESD-Zener diode: 6.1 V typ., max 5.0 mA; R_{ST(ON)} < 375 Ω at 1.6 mA. The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

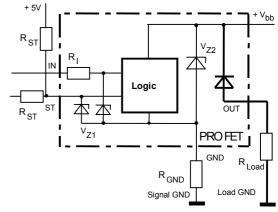
Inductive and overvoltage output clamp





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Overvolt. and reverse batt. protection

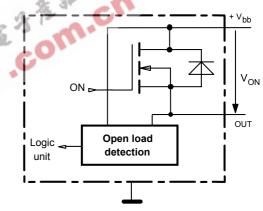


 V_{Z1} = 6.1 V typ., V_{Z2} = 47 V typ., R_{GND} = 150 Ω, R_{ST} = 15 kΩ, R_{I} = 3.5 kΩ typ.

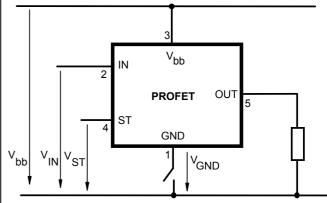
In case of reverse battery the load current has to be limited by the load. Temperature protection is not active

Open-load detection in on-state





GND disconnect

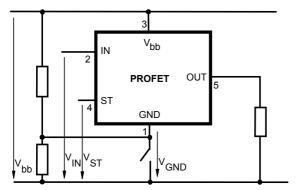


Any kind of load. In case of Input=high is $V_{OUT} \approx V_{IN} - V_{IN(T+)}$. Due to V_{GND} >0, no V_{ST} = low signal available.



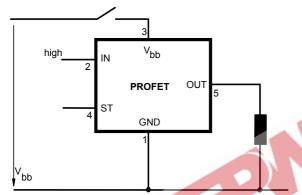
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GND disconnect with GND pull up



Any kind of load. If V_{GND} > V_{IN} - $V_{IN(T+)}$ device stays off Due to V_{GND} >0, no V_{ST} = low signal available.

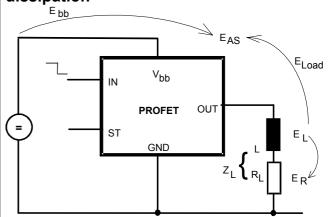
$V_{bb}\xspace$ disconnect with energized inductive load



For inductive load currents up to the limits defined by Z_L (max. ratings and diagram on page 8) each switch is protected against loss of V_{bb} .

Consider at your PCB layout that in the case of Vbb disconnection with energized inductive load all the load current flows through the GND connection.

Inductive Load switch-off energy dissipation



Energy stored in load inductance:

$$\Xi_{\rm L} = \frac{1}{2} \cdot {\rm L} \cdot {\rm I}_{\rm L}^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

with an approximate solution for $R_L > 0 \Omega$:

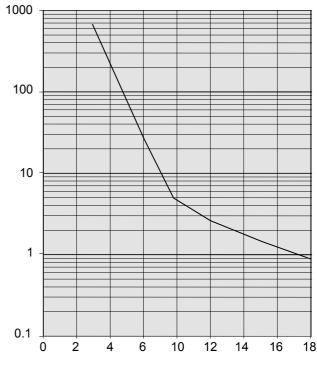
$$E_{AS} = \frac{I_{L} \cdot L}{2 \cdot R_{L}} (V_{bb} + |V_{OUT(CL)}|) \cdot ln (1 + \frac{I_{L} \cdot R_{L}}{|V_{OUT(CL)}|})$$

Maximum allowable load inductance for a single switch off

 $L = f(I_L); T_{j,start} = 150^{\circ}C, T_C = 150^{\circ}C \text{ const.},$ $V_{bb} = 12 \text{ V}, R_L = 0 \Omega$

 Z_L [mH]

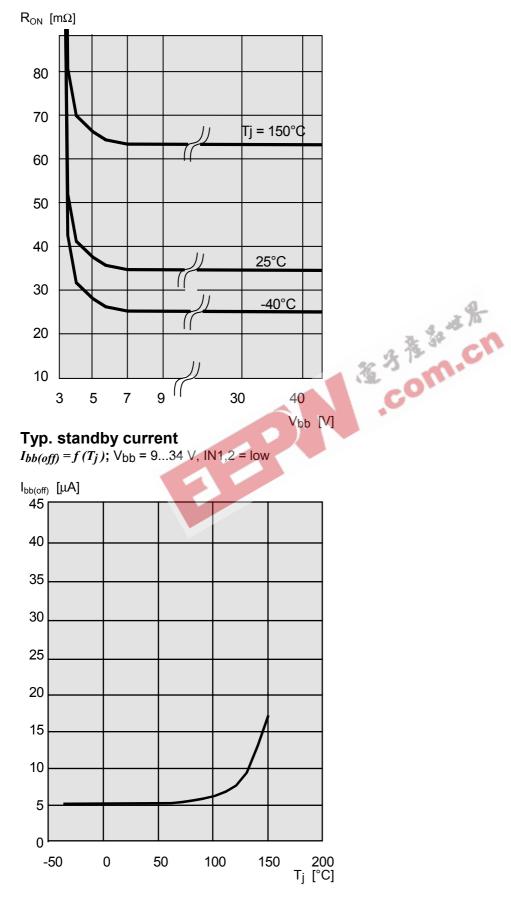
61





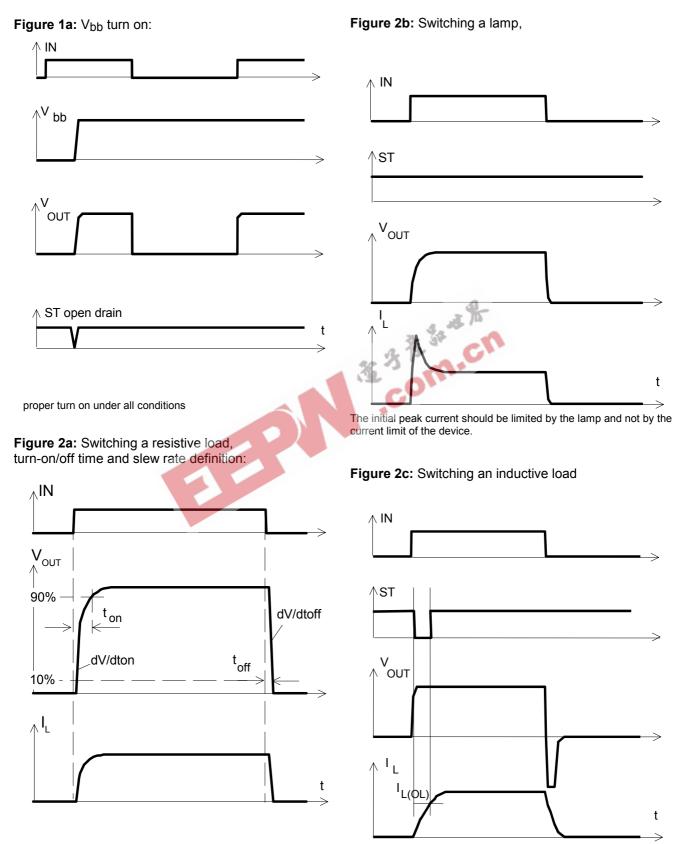
Typ. on-state resistance

 $R_{ON} = f(V_{bb}, T_i); I_L = 2A, IN = high$





Timing diagrams



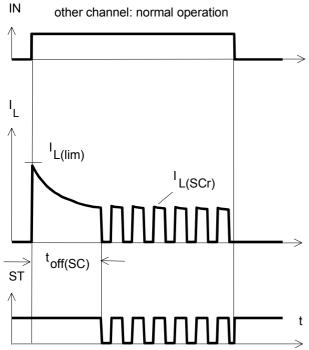
*) if the time constant of load is too large, open-load-status may occur



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Figure 3a: Short circuit

shut down by overtemperature, reset by cooling



Heating up of the chip may require several milliseconds, depending on external conditions

Figure 4a: Overtemperature: Reset if $T_i < T_{jt}$

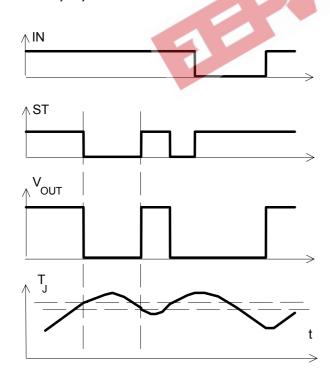


Figure 5a: Open load: detection in ON-state, open load occurs in on-state

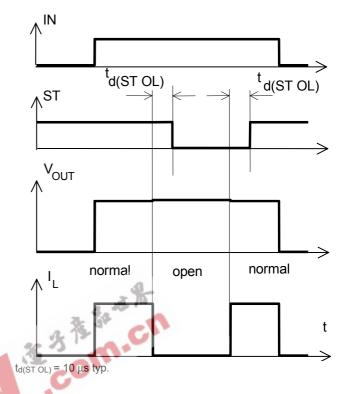
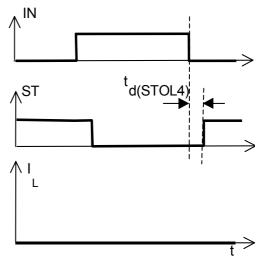


Figure 5b: Open load: turn on/off to open load



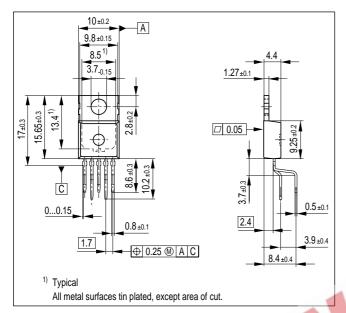


Package and Ordering Code

All dimensions in mm

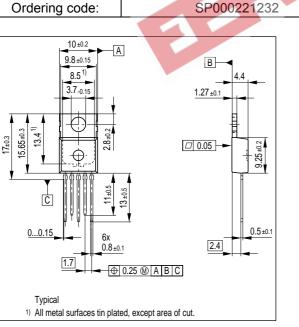
Standard (=staggered): PG-TO220-5-11

Sales code	ITS436L2
Ordering code:	SP000221231



Straight: PG-TO220-5-12

Sales code



ITS436L2 S

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